Unit in mm

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2 S A 1 4 5 1 A

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

- Low Collector Saturation Voltage
 - : $V_{CE (sat)} = -0.4V (Max.) (at I_{C} = -6A)$
- $\bullet \qquad \text{High Speed Switching Time} \, : \, t_{\mbox{stg}} \! = \! 1.0 \mu \mbox{s} \, (\mbox{Typ.})$
- Complementary to 2SC3709A

MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	-60	V
Collector-Emitter Voltage	v_{CEO}	-50	V
Emitter-Base Voltage	v_{EBO}	-6	V
Collector Current	$I_{\mathbf{C}}$	-12	A
Base Current	$I_{\mathbf{B}}$	-2	A
Collector Power Dissipation (Tc=25°C)	PC	30	w
Junction Temperature	$T_{ m j}$	150	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C

1. BASE
2. COLLECTOR
3. EMITTER

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TOSHIBA

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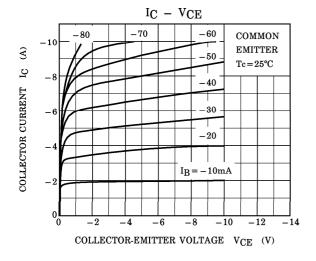
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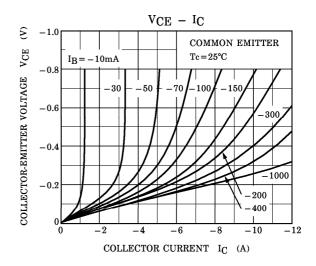
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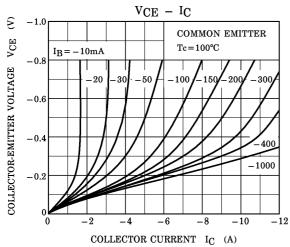
ELECTRICAL CHARACTERISTICS (Tc = 25°C)

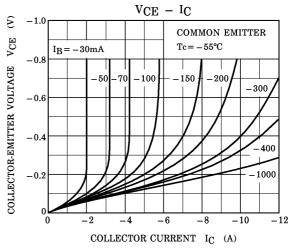
CHARA	ACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cu	ut-off Current	I_{CBO}	$V_{CB} = -60V, I_{E} = 0$	_	_	-10	μ A
Emitter Cu	t-off Current	I_{EBO}	$V_{EB} = -6V, I_{C} = 0$		_	-10	μ A
Collector-Er Breakdown		V (BR) CEO	$I_{C} = -50 \text{mA}, I_{B} = 0$	-50	_	_	V
DC Current Gain		hFE (1) (Note)	$V_{CE} = -1V, I_{C} = -1A$	70	_	240	
		h _{FE (2)}	$V_{CE} = -1V, I_{C} = -6A$	40	_	_	
Saturation Collector Voltage Base-En	Collector-Emitter	V _{CE} (sat)	$I_C = -6A, I_B = -0.3A$	_	-0.15	-0.4	V I
	Base-Emitter	V _{BE} (sat)	$I_C = -6A, I_B = -0.3A$	_	-0.9	-1.2	
Transition Frequency		${ m f_T}$	$V_{CE} = -5V, I_{C} = -1A$	_	70	_	MHz
Collector Output Capacitance		C _{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	_	320	_	рF
Switching Time	Turn-on Time	ton	$\begin{array}{c c} 20 \mu s & \text{INPUT} & \underline{I_{B2}} & \text{OUTPUT} \\ I_{B1} & \underline{I_{B2}} & \underline{I_{B1}} & \underline{V_{CC}} & \underline{=} -30V \\ -I_{B1} = I_{B2} = 0.3A & \underline{V_{CC}} & \underline{=} -30V \\ DUTY & CYCLE \leq 1\% & \underline{} & $	_	0.3	_	
	Storage Time	$t_{ m stg}$			1.0	_	μ s
	Fall Time	t_f		_	0.2	_	

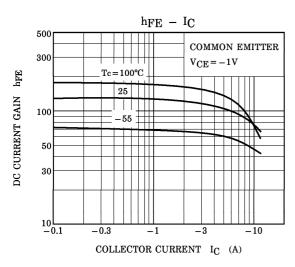
(Note) hFE (1) Classification O : 70~140, Y : 120~240

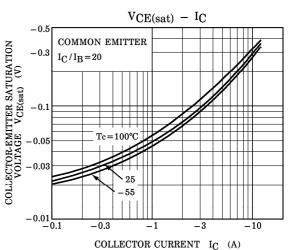




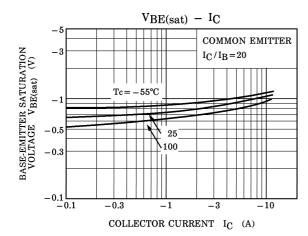


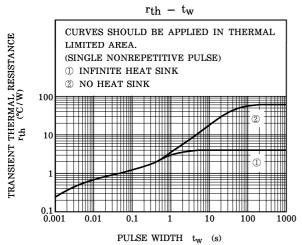


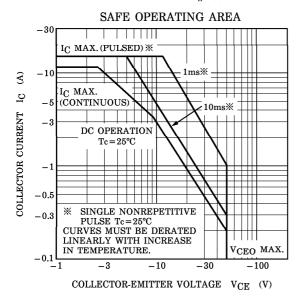


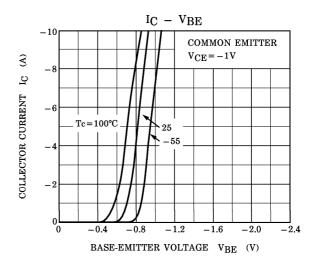


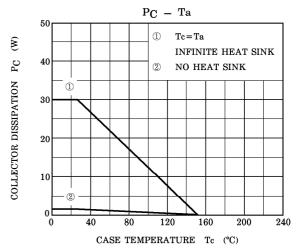
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